

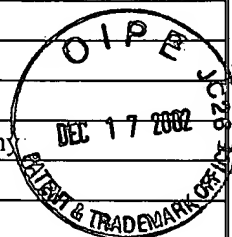
Substitute for Form 1449A/PTO (Modified)

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	09/831,539
Filing Date	04/15/2002
First Named Inventor:	Anand S. Murthy
Group Art Unit	2823
Examiner Name	Kebede, Brook
Attorney Docket Number	42390P6624US



Sheet

1

of

2

Attorney Docket Number

42390P6624US

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

Examiner
Signature

Brook Kikell

Date Considered

3/8/2002

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard S.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.**

Substitute for Form 1449A/PTO (Modified) INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	09/831,539
				Filing Date	04/15/2002
				First Named Inventor:	Anand S. Murthy
				Group Art Unit	2823
				Examiner Name	Kebede, Brook
				Attorney Docket Number	42390P6624US
Sheet	2	of	2		
OTHER ART - NO PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
BK		MITANI, Y., ET AL., Buried Source and Drain (BSD) Structure for Ultra-shallow Junction Using Selective Deposition of Highly Doped Amorphous Silicon, 1996 Symposium on VLSI Technology, Digest of Technical Papers, Honolulu, The IEEE Electron Devices Society, The Japan Society of Applied Physics, IEEE CAT No. 96CH35944, JSAP CAT. No. AP961207, ©1996 IEEE, pages 176-177.			
		<hr/>			
BK		NAKAHARA, Y., ET AL., Ultra-shallow in-situ-doped raised source/drain structure for sub-tenth micron CMOS, 1996 Symposium on VLSI Technology Digest of Technical Papers, ©1996 IEEE, pages 174-175.			
		<hr/>			
BK		UCHINO, TAKASHI, ET AL., A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1-µm CMOS ULSIs, ©1997 IEEE, pgs. 479-482.			
		<hr/>			
BK		WOLF, S. AND TAUBER, R.N., for the VLSI Era, Volume 1 - Process Technology, pages 173-174 and pages 545-547.			
		<hr/>			
BK		Search Report for PCT/US99/26224, mailed February 10, 2000, 5 pages.			
		<hr/>			
BK		Written Opinion for PCT/US99/26224, mailed October 30, 2000, 4 pages.			
		<hr/>			

Examiner Signature	<i>Brook Kebede</i>	Date Considered	<i>3/8/2003</i>
--------------------	---------------------	-----------------	-----------------

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹Unique citation designation number. ²Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office,